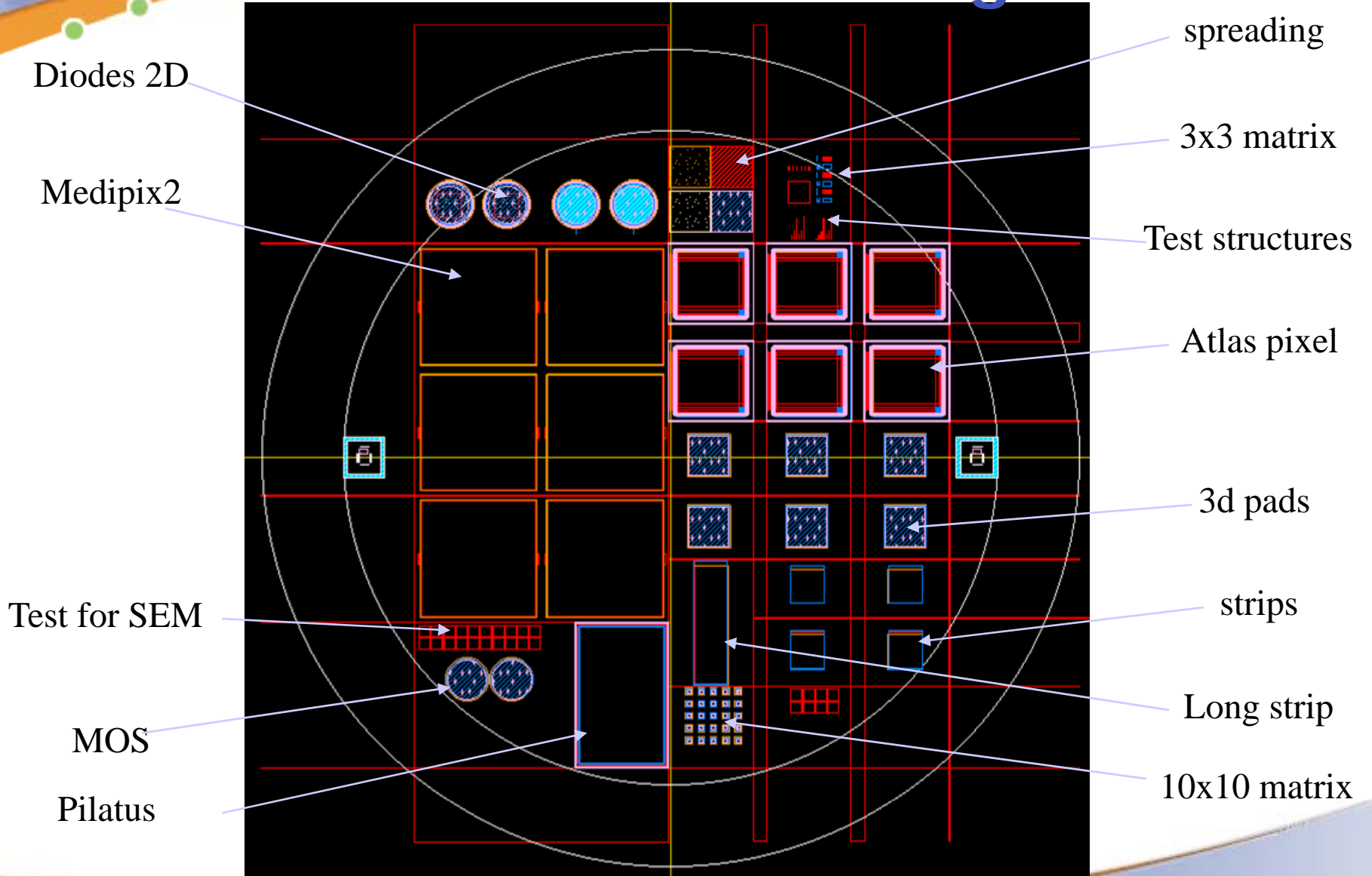


Report from CNM activities

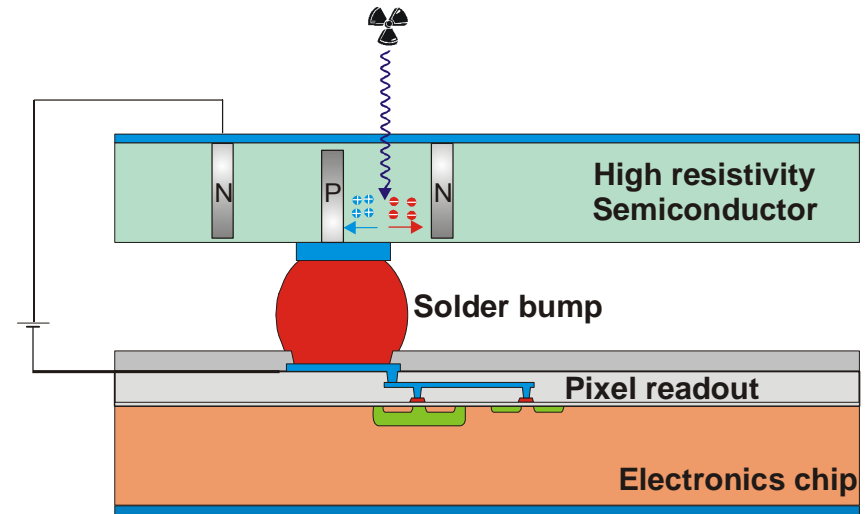
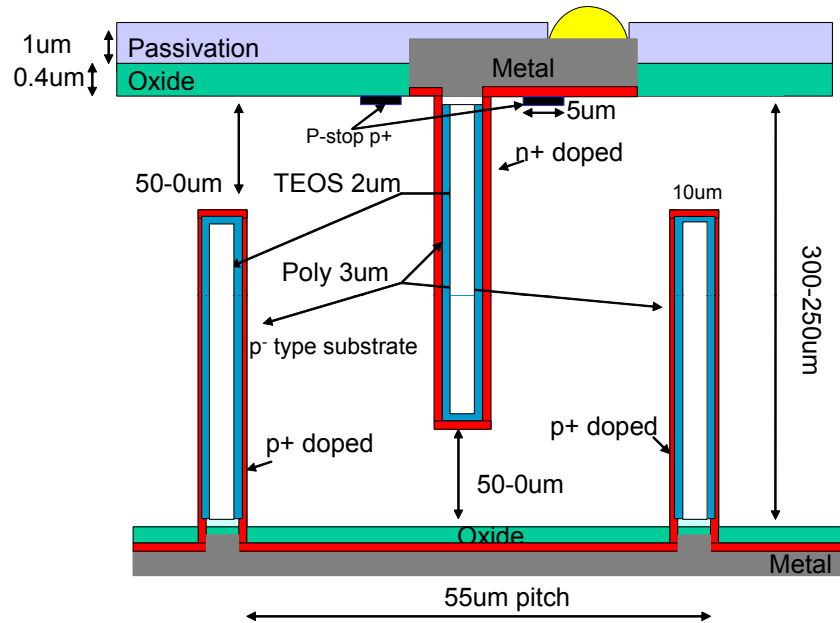
Giulio Pellegrini

Centro Nacional de Microelectronica
Barcelona, Spain

Mask design

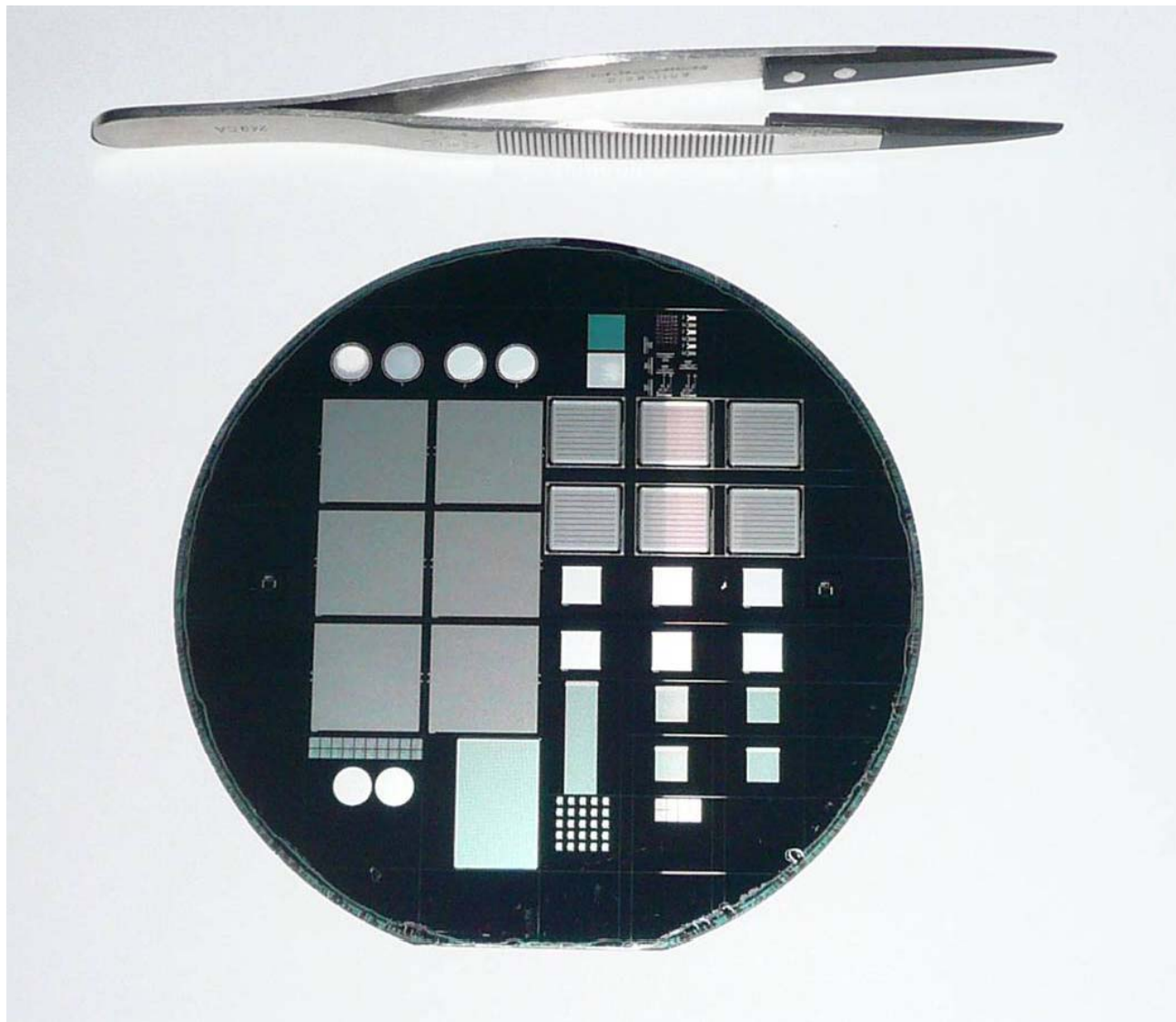


Layout



- 3 detectors have been bump bonded in VTT to a Medipix2 chip.
- 3 more to do.
- Strip detectors irradiated with neutrons: fluence $5E15 \text{ cm}^{-2}$

Fabricated detectors



Double sided 3D

First run is p-in-n:

- 250 μm p+ columns in 300 μm n-type substrate

Electrode fabrication:

1. ICP etching of the holes: Bosch process, ALCATEL 601-E
2. Holes partially filled with 3 μm LPCVD poly
3. Doping with P or B
4. Holes passivated SiO_2

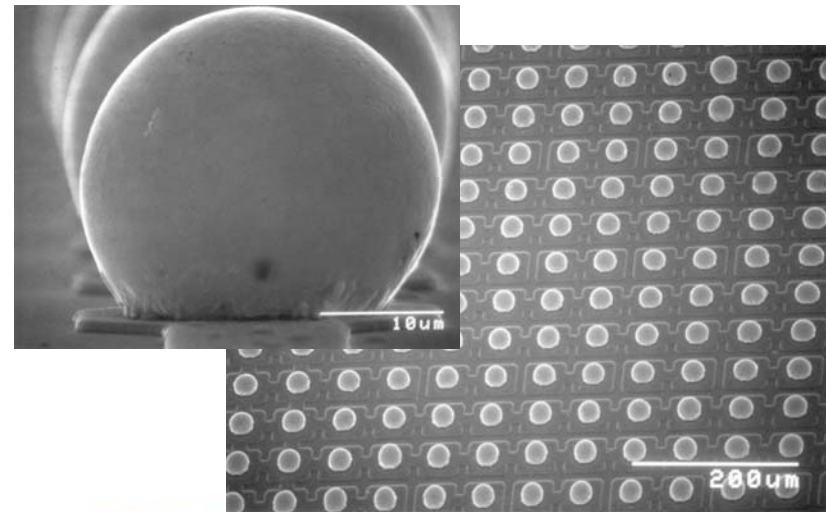
(all fabrication done in-house)



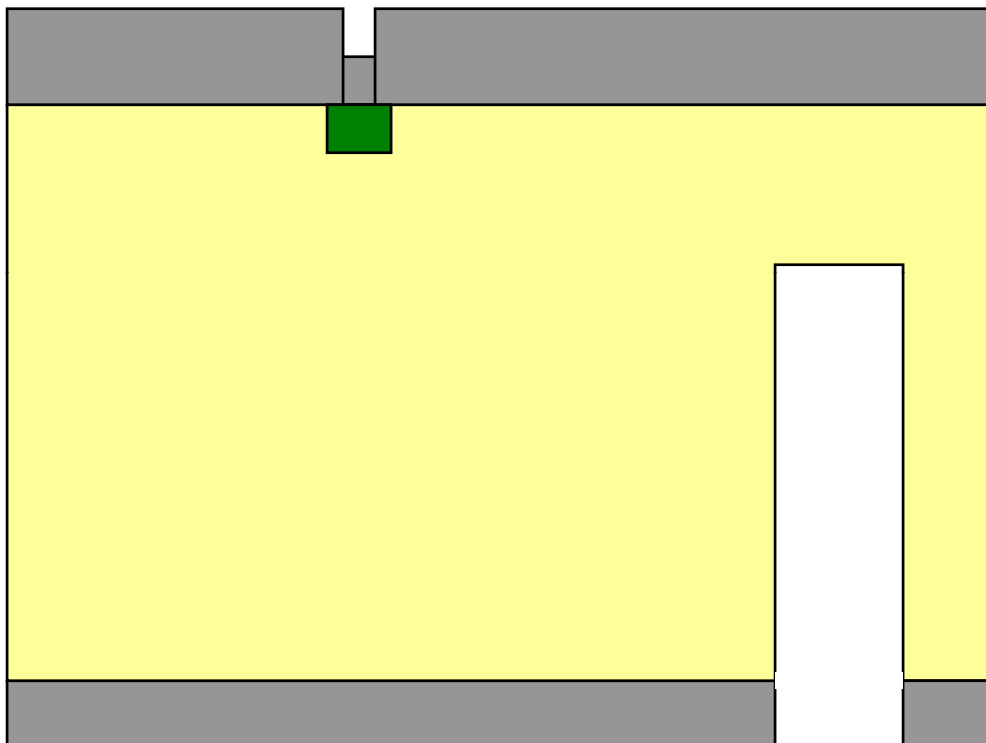
- Deep RIE-ICP.
- Load-lock manual one 4" wafer
- SF_6 etching
- C_4F_8 passivation
- Cooled mechanical clamping :He-Ln2
- Possibility of Cryogenic etching.

Bump bonding at CNM

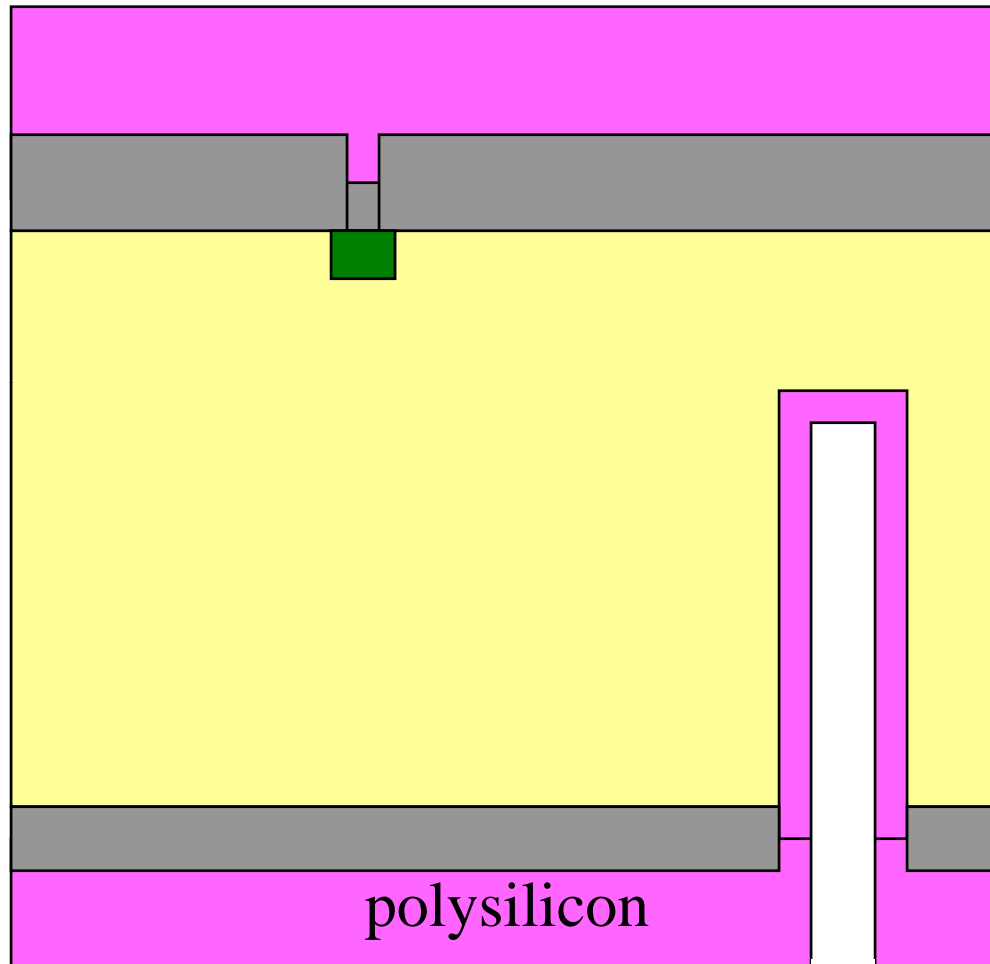
- Small clean room class 100 at CNM dedicated to packaging: Flip chip, Wire bonding, CMP
- Joint project with IFAE (High Energy Physics Institute)
- Bump bonding machine Süss Microtech FC150
Installation finished last month, in operation.
- Bumping process ready: electrodeposited SnPb and SnAg
- CMP G&P POLI-400L (Installation pending)



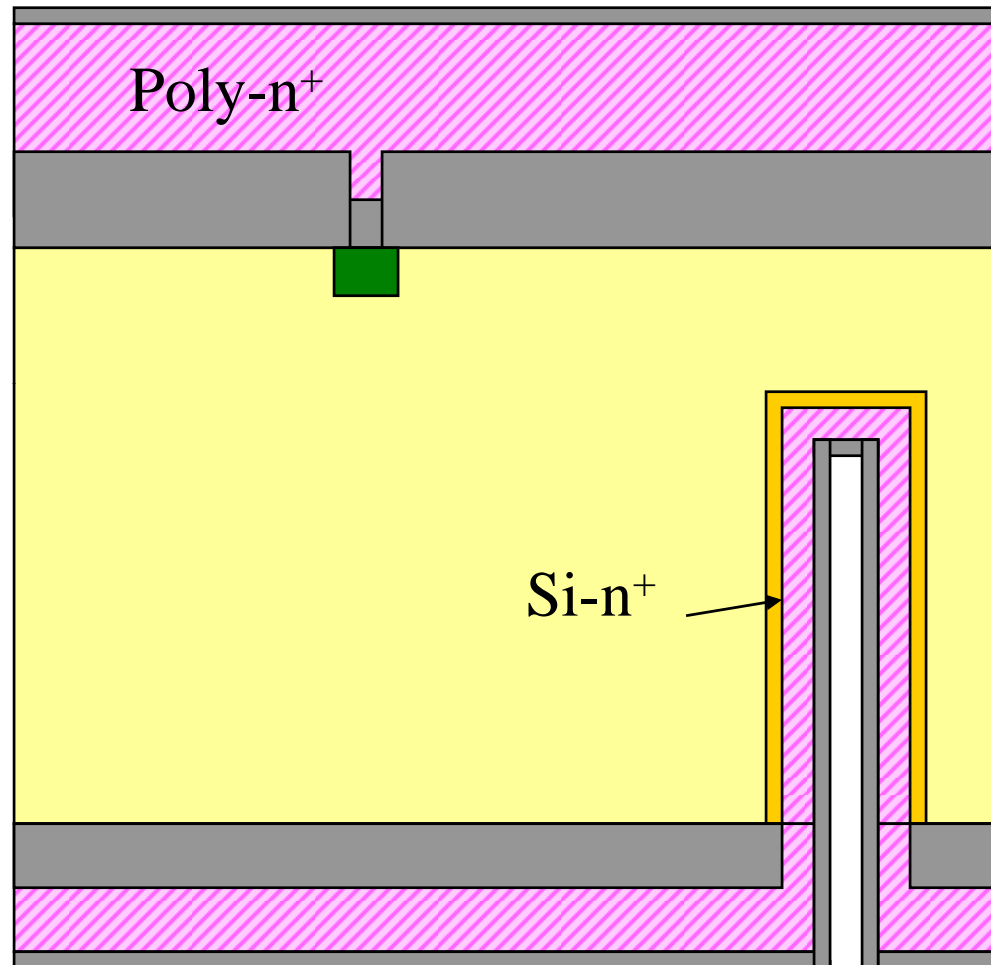
Holes etching



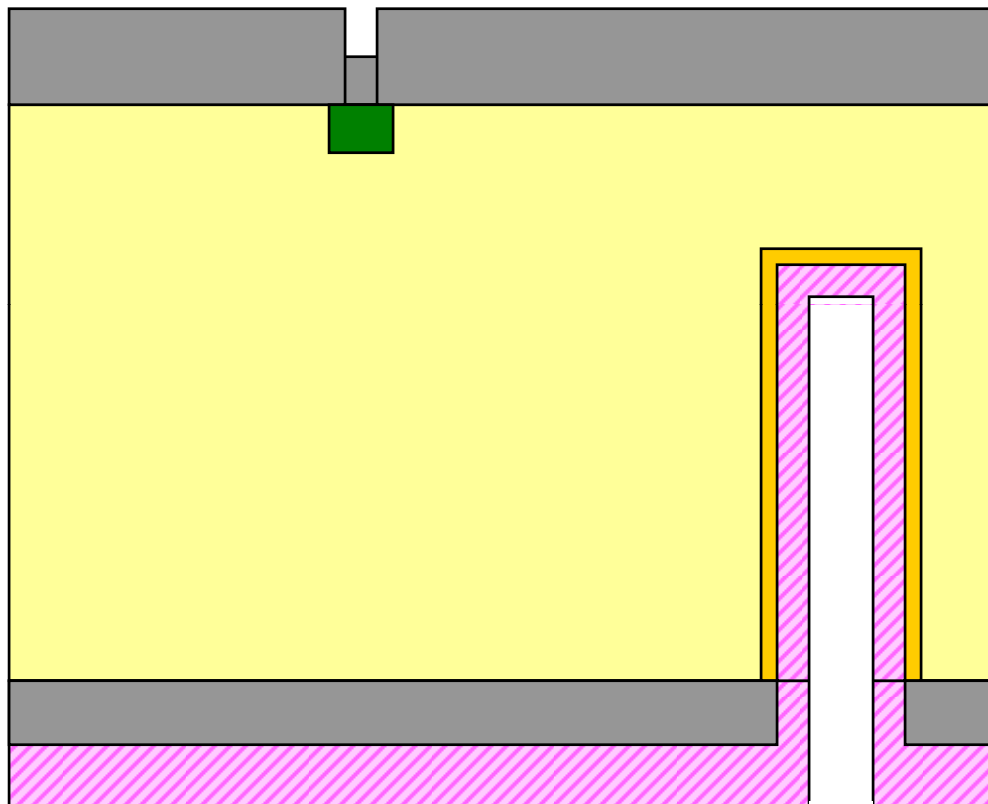
Poly filling



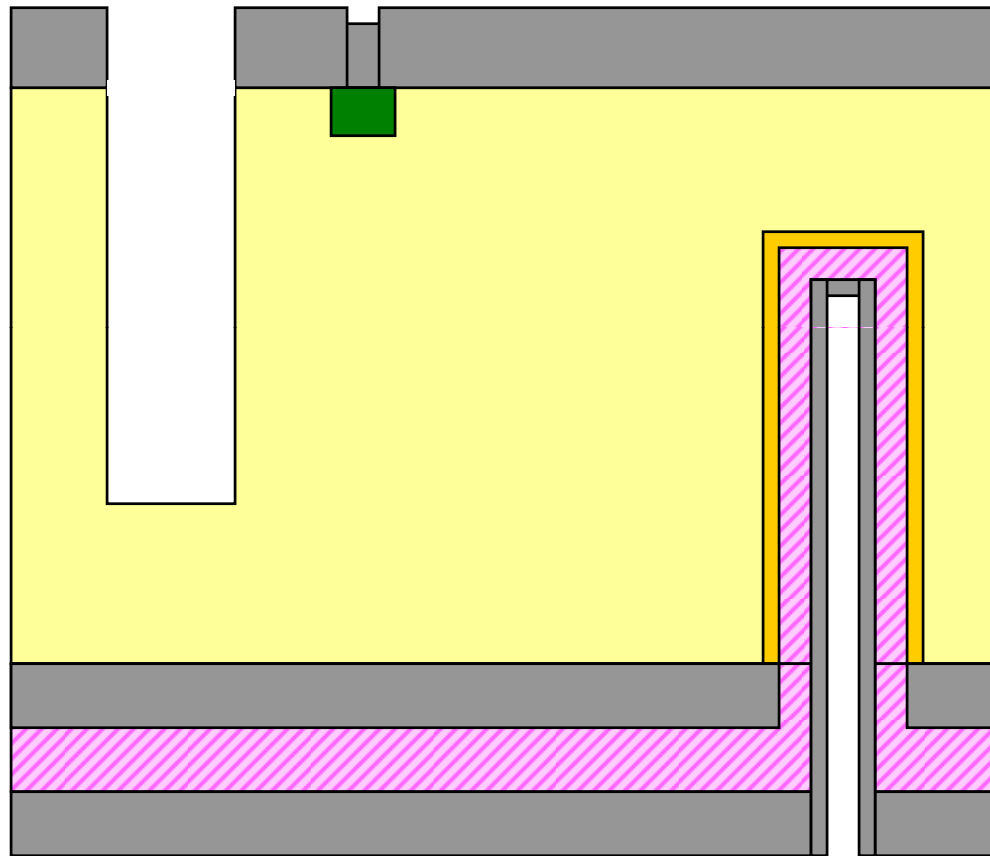
Doping of poly



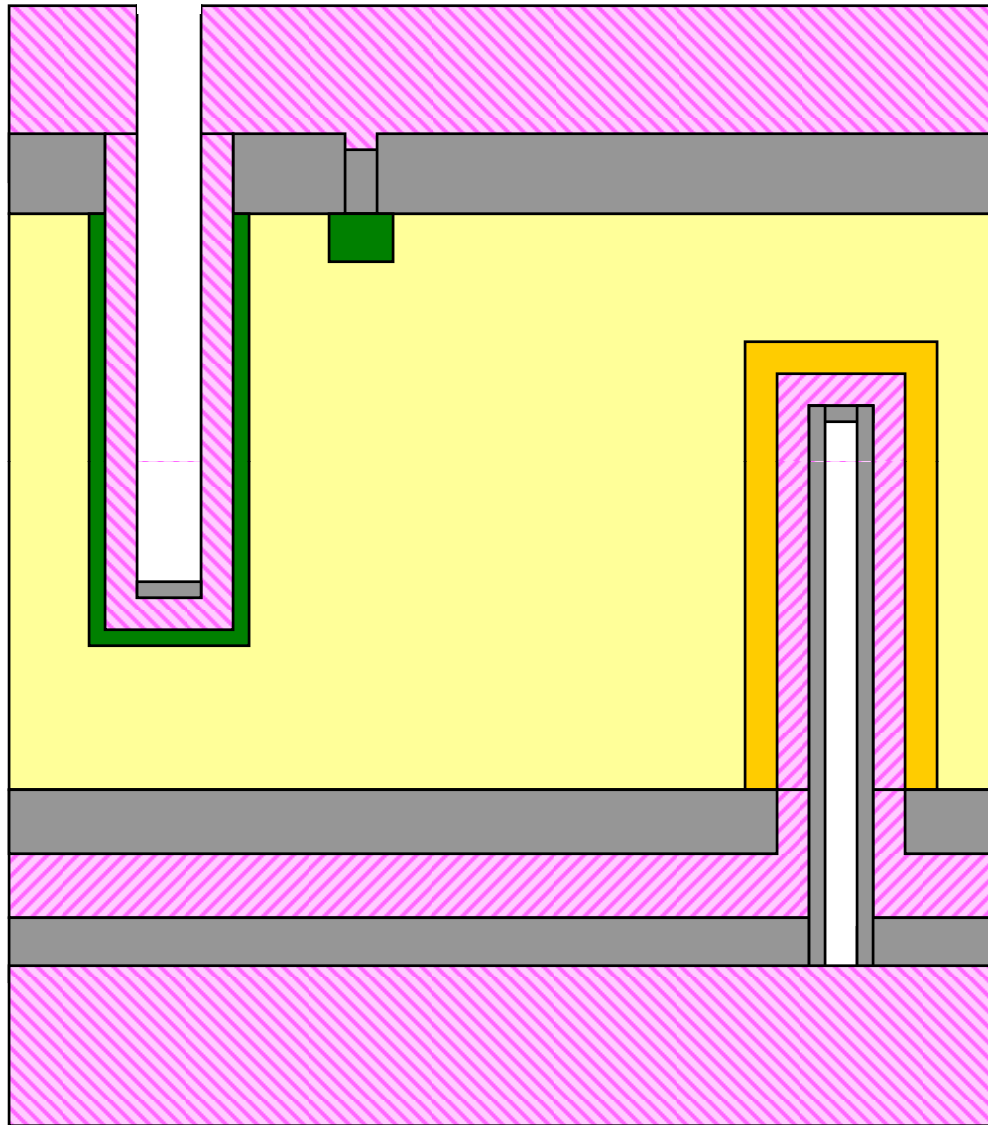
Poly etching



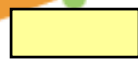







Second etching



Second poly filling

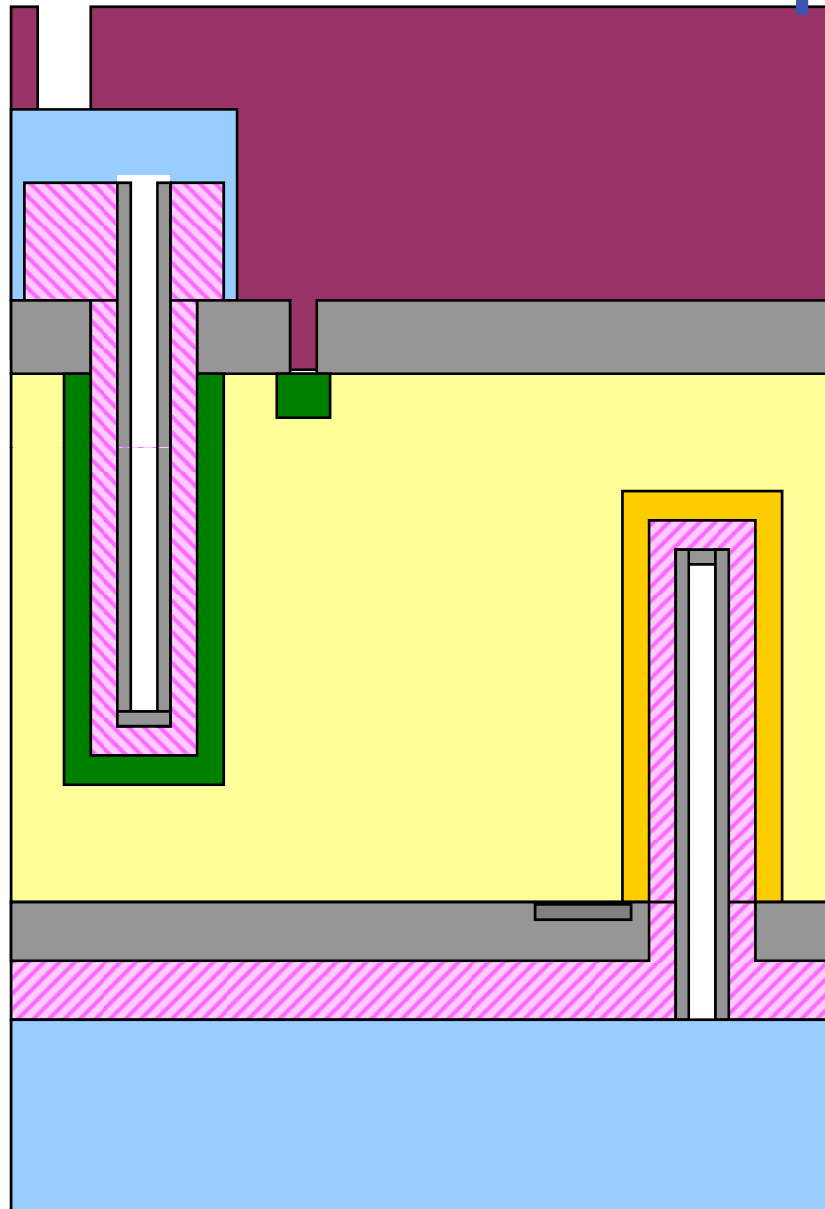


Final sample

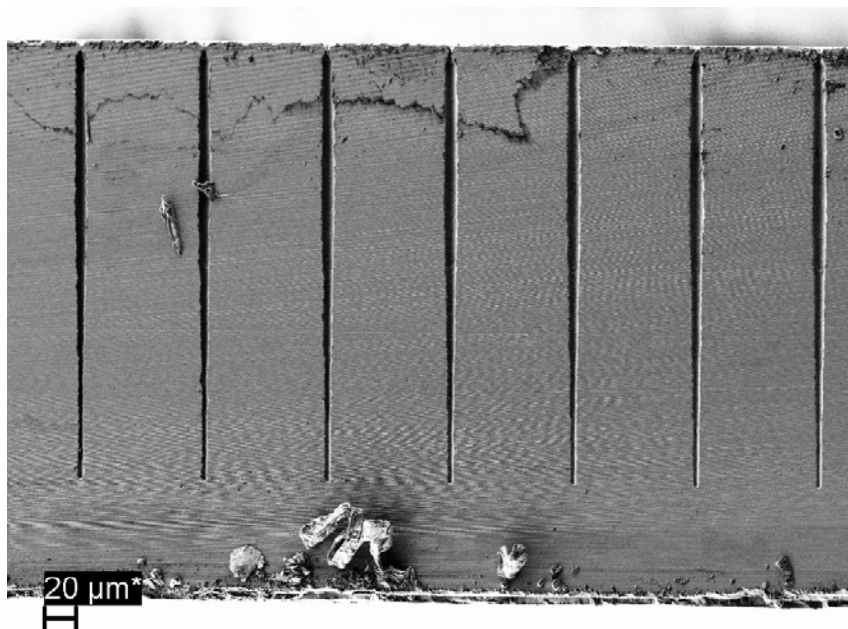
-  Si-n⁻
-  Si-p⁺
-  Si-n⁺
-  SiO₂
-  Poly-p⁺
-  Poly-n⁺
-  Al/Cu
-  Passiv

Mask Levels

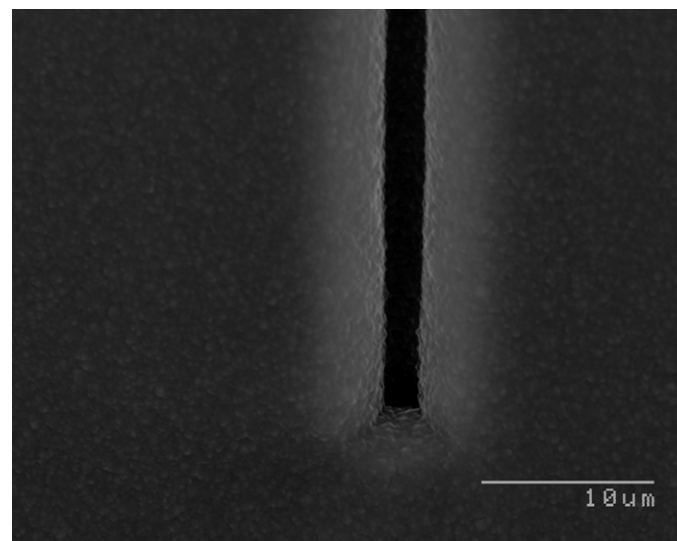
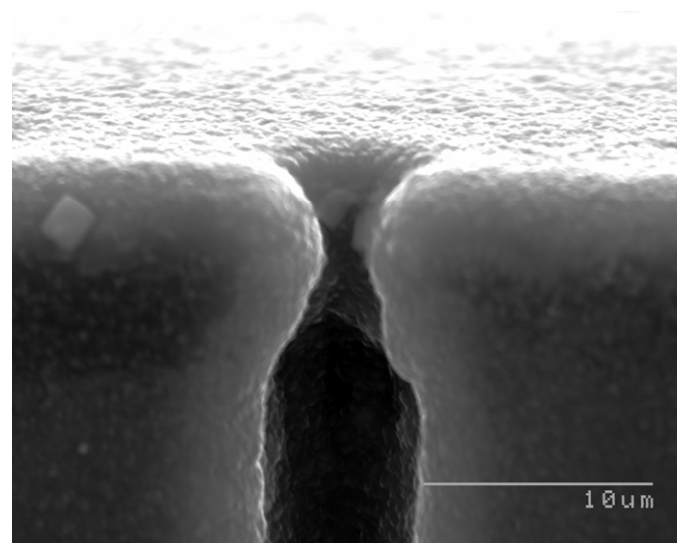
- Back-window
- N-DIFF
- N-HOLES
- P-HOLES
- POLY
- WINDOW
- METAL
- PASSIV
- Bump bonding



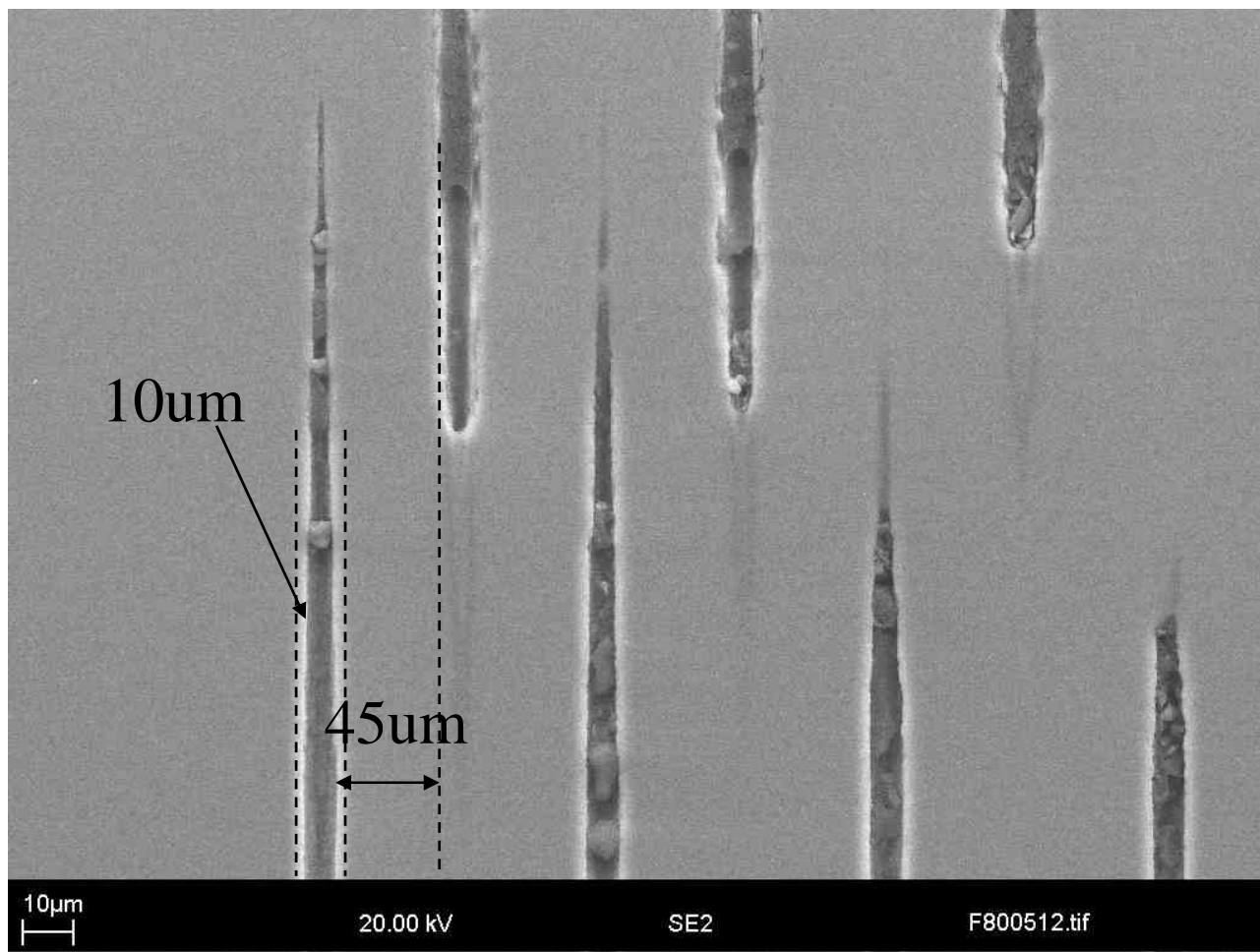
3D technology



- 10 μm holes
- 55 μm pitch
- 90 minutes etching
- 300 μm thick wafer
- Aspect ratio 24:1

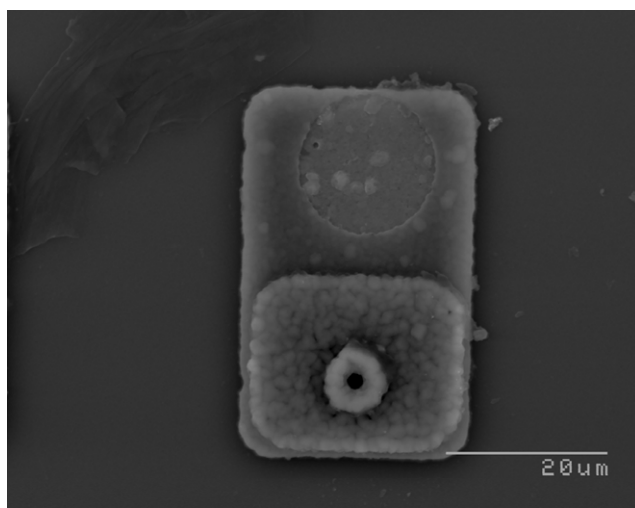
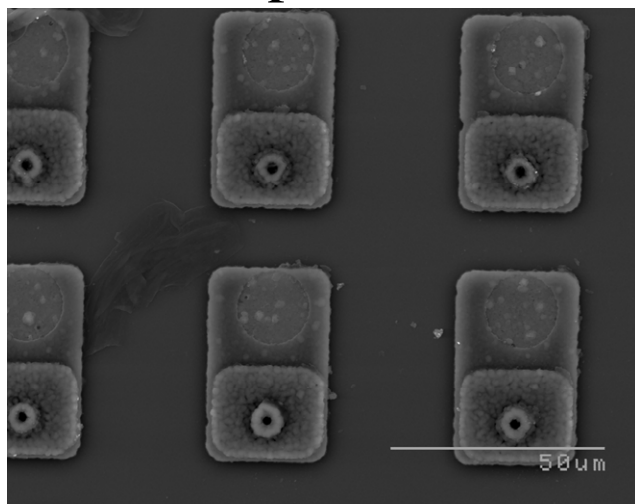


3D technology

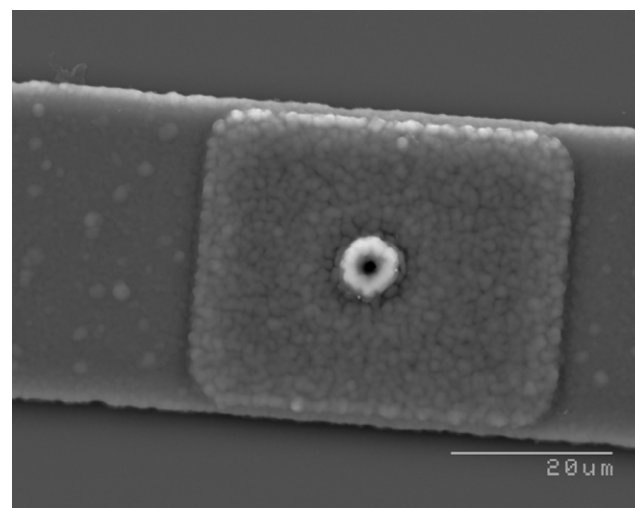
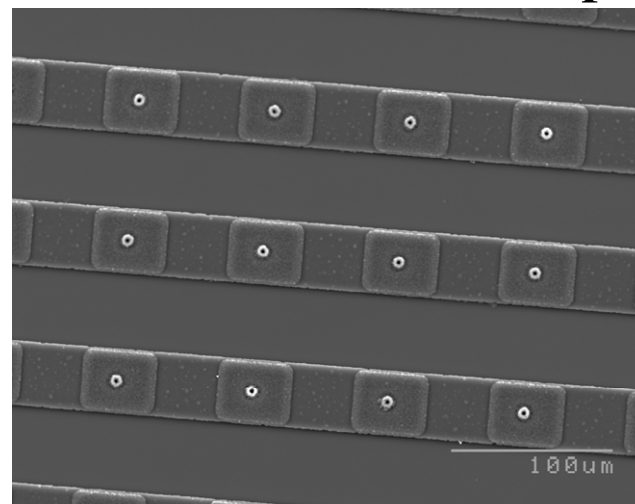


3D technology

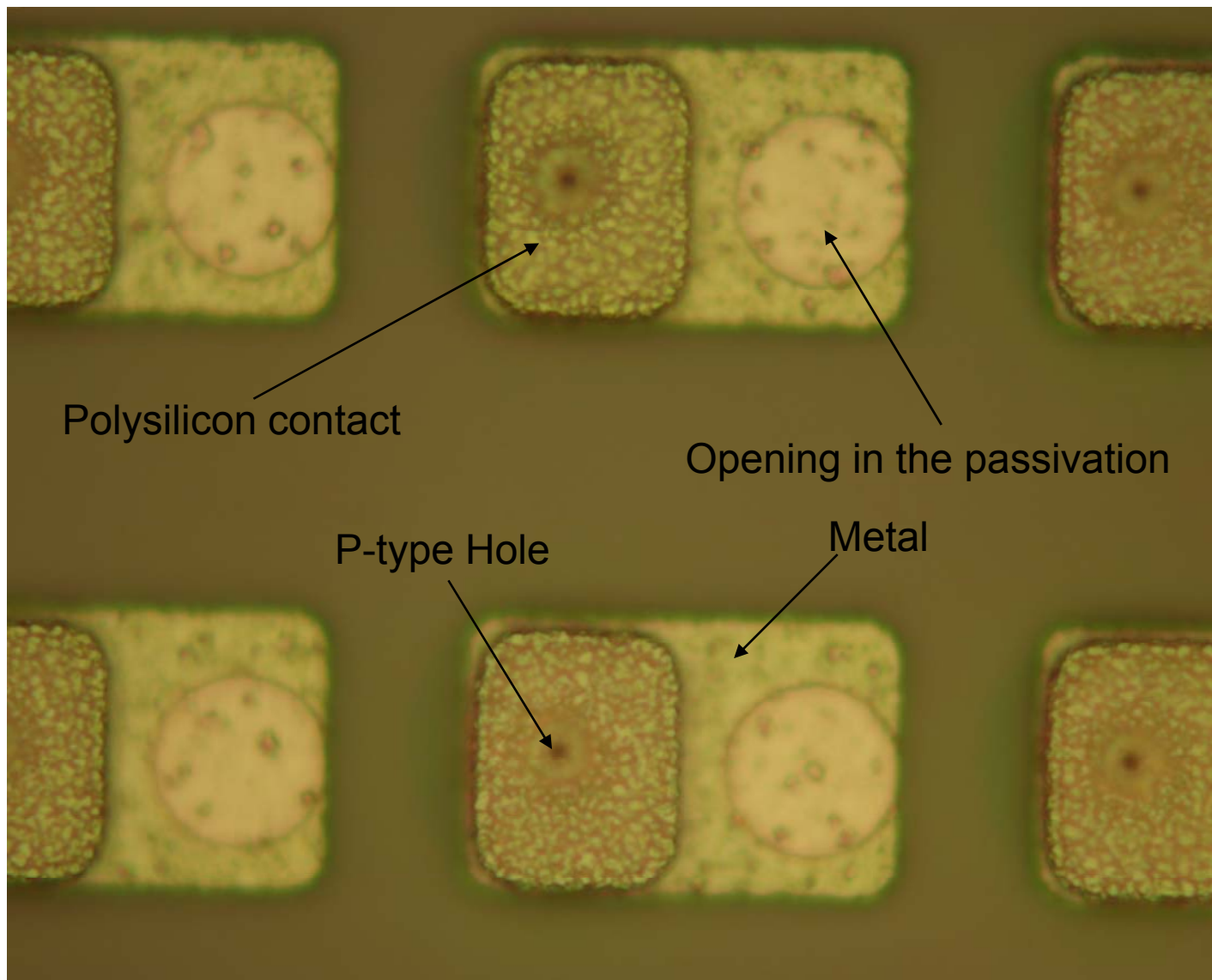
pixels



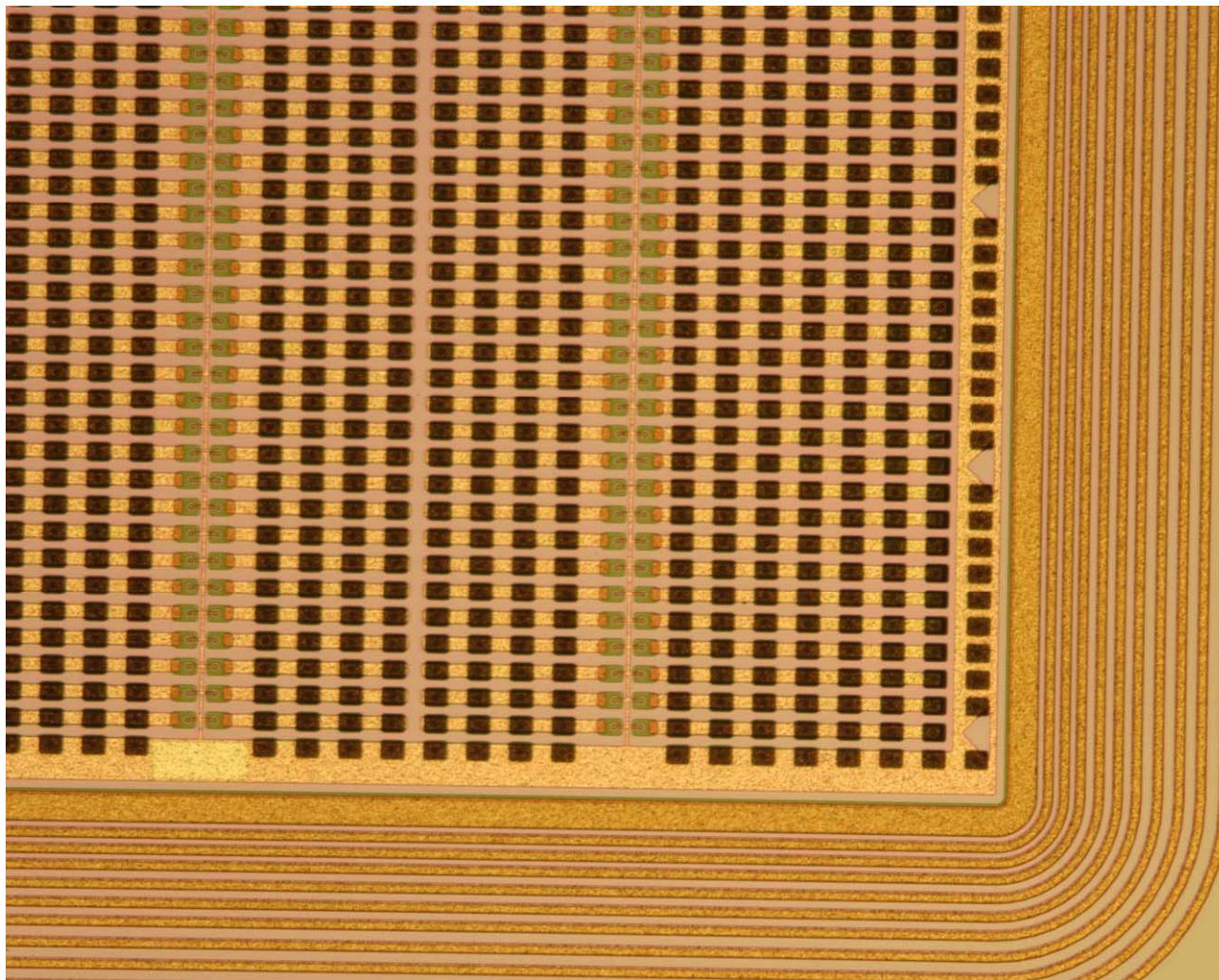
strips



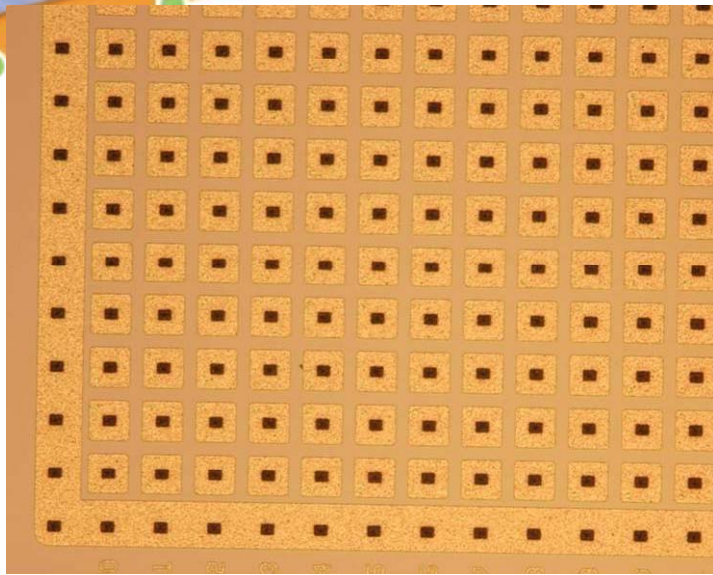
Pixel configuration



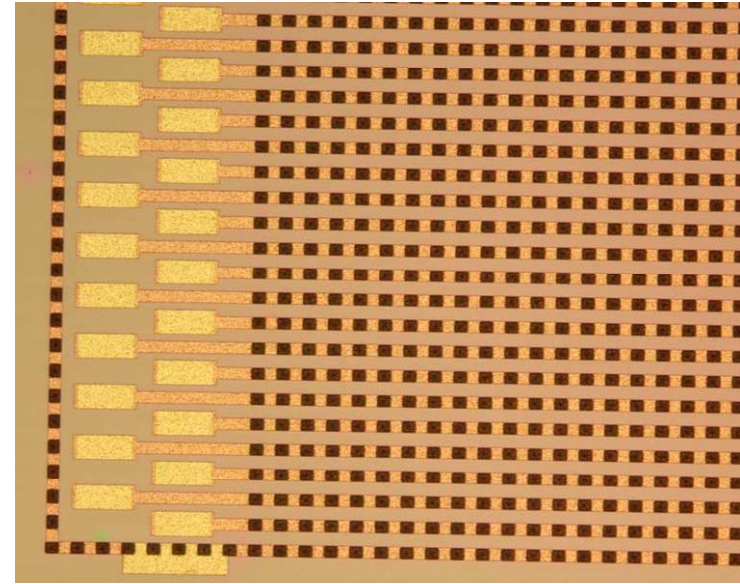
Atlas pixels



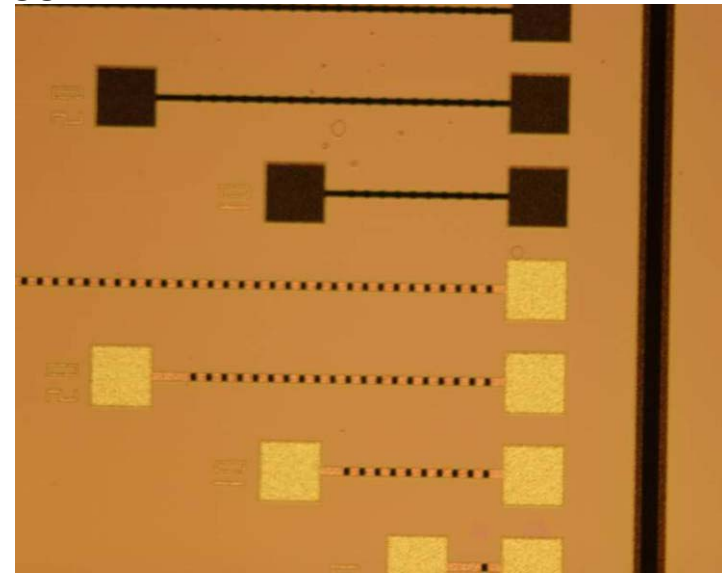
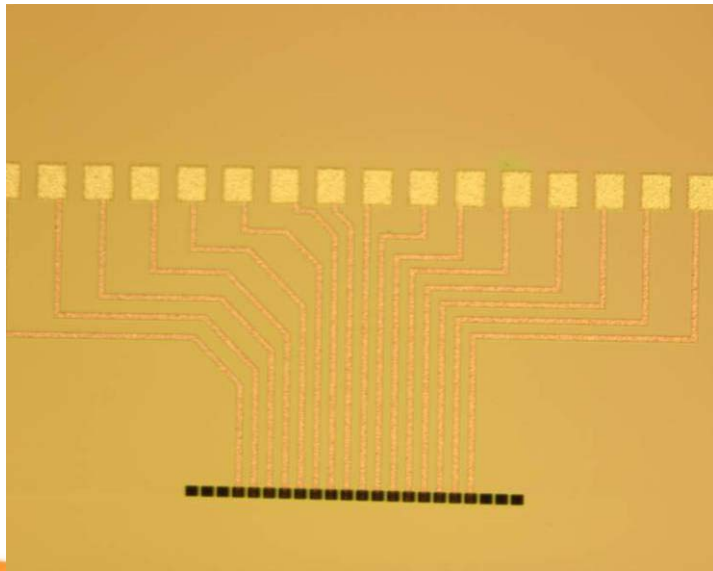
Pilatus



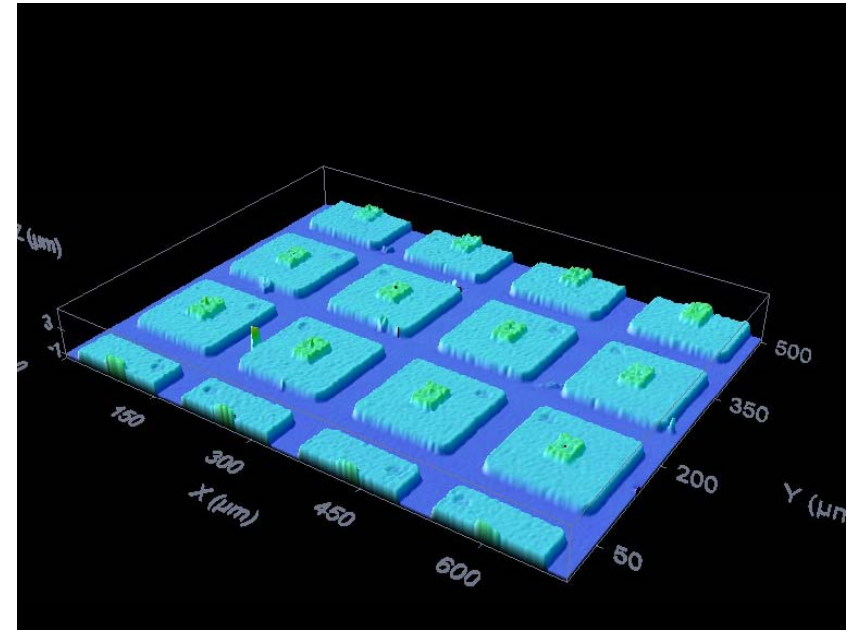
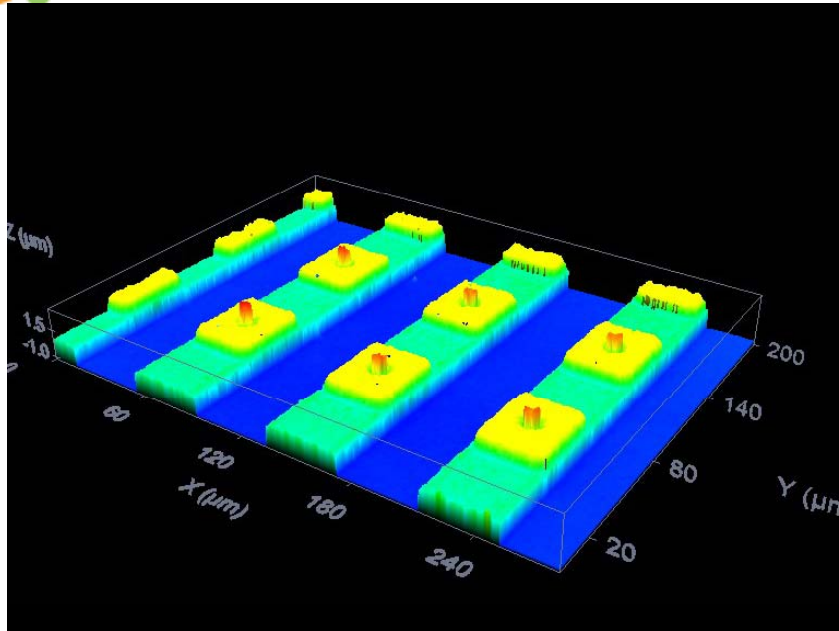
Strips (DC coupled)



Test structures



Optical Profiler



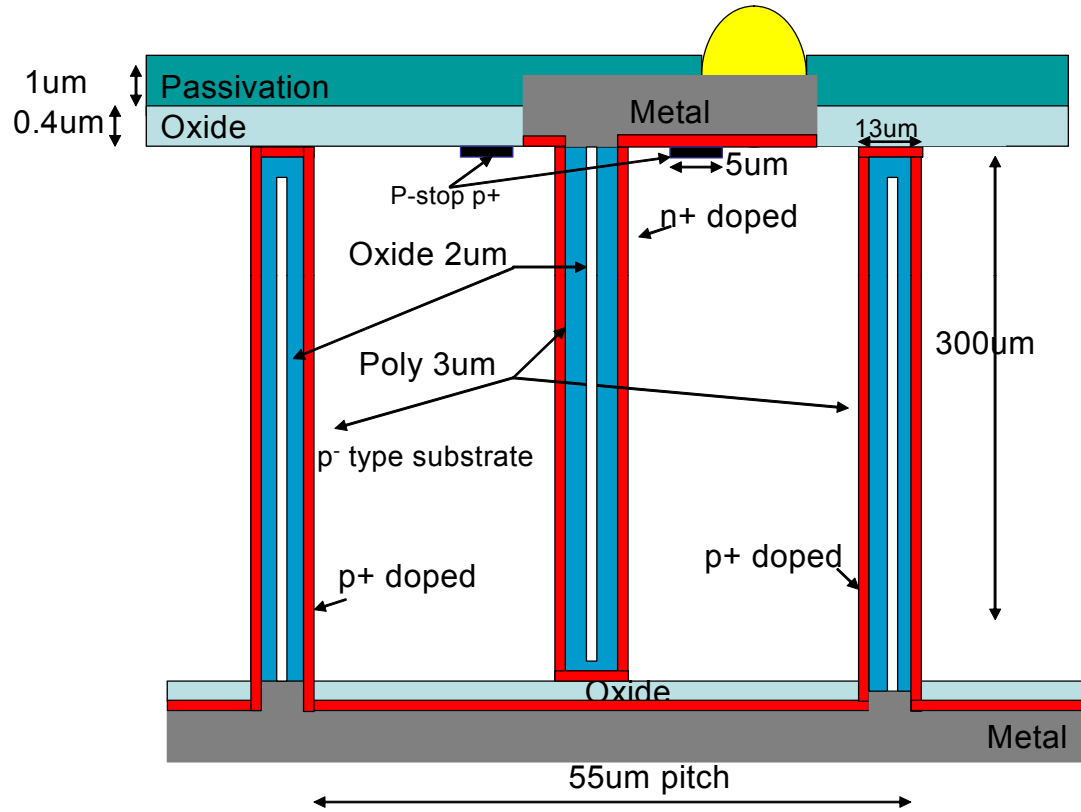
Total bending: in strip detector we measured a curvature of $0.6 \mu\text{m}$
In Pixel detector VTT measured a bending of $3 \mu\text{m}$.

Testing

- Charge Collection Efficiency
- Electrical characterization
- Imaging with Medipix2 chip
- Irradiation with neutrons

please see Chris Parkes' talk

New Fabrication Run



8 wafers p-type
8 wafers n-type

In Fabrication, due for the end of June 2008

Thank you